

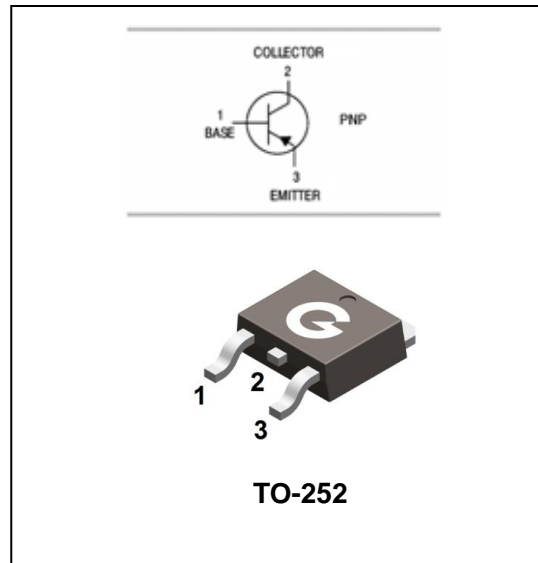
PNP Epitaxial Planar Silicon Transistors

2SB1202

FEATURES

- Adoption of FBET, MBIT processes
- Large current capacity and wide ASO
- Low collector-to-emitter saturation voltage
- Fast switching speed
- Small and slim package making it easy to
Make 2SB1202-used sets smaller

HF



APPLICATIONS

- High-Current Switching Applications
- Voltage regulators, relay drivers, lamp drivers,
Electrical equipment

Ordering Information

Part Number	Package	Shipping	Marking Code
2SB1202	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	B1202

MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-3	A
I_{CP}	Collector Power Dissipation	-6	A
P_C	Collector Power Dissipation	1	W
T_J, T_{STG}	Junction and Storage temperature range	-55 to +150	°C

PNP Epitaxial Planar Silicon Transistors

2SB1202

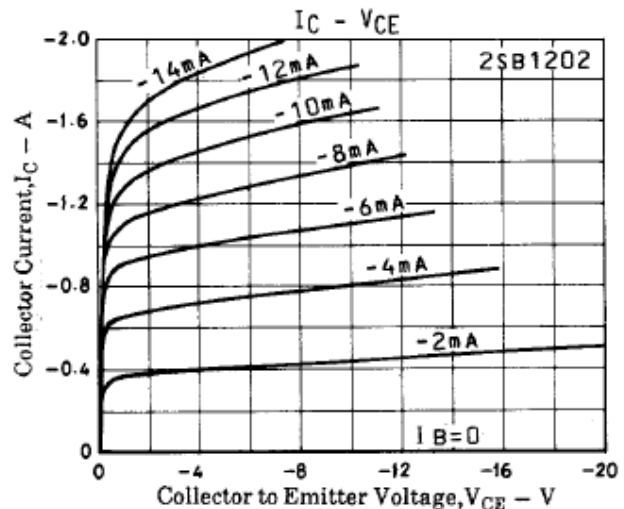
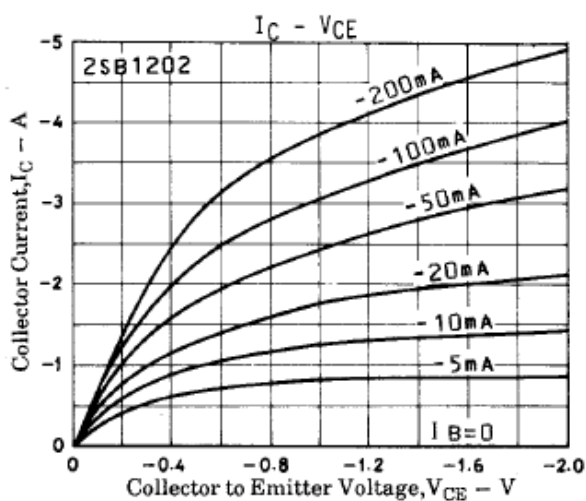
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EBO} = -4\text{V}, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -100\text{mA}$ $V_{CE} = -2\text{V}, I_C = -3\text{A}$	100 35		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.1\text{A}$		-0.35	-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -0.1\text{A}$		-0.94	-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_E = -50\text{mA}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		39		pF

CLASSIFICATION OF $h_{FE(1)}$

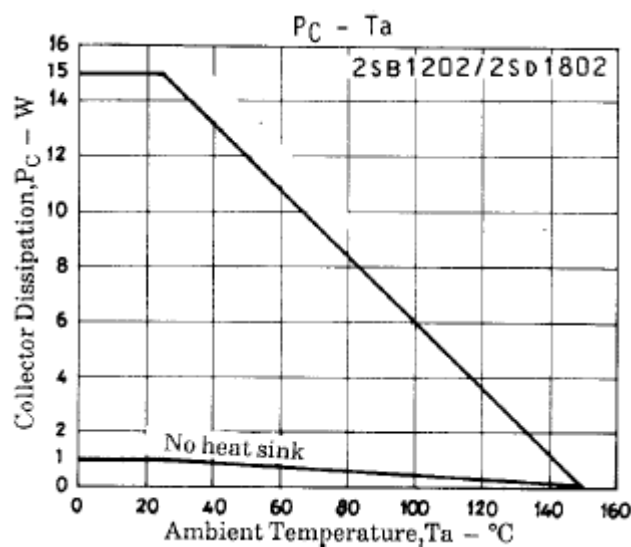
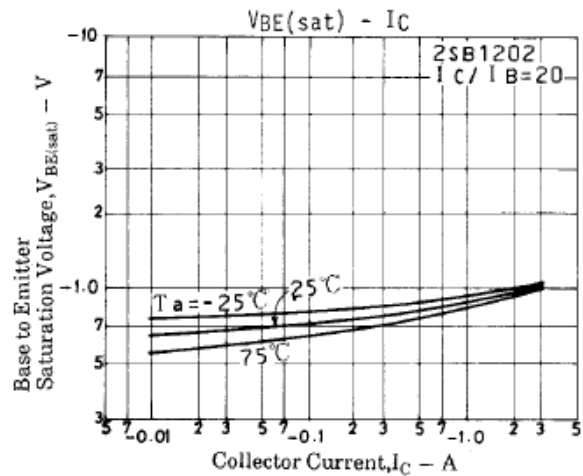
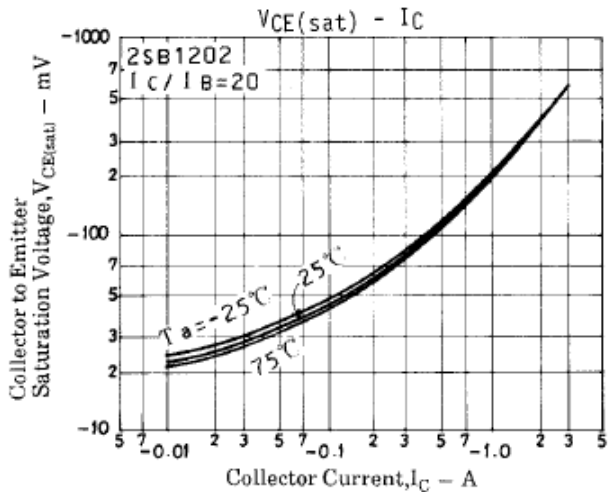
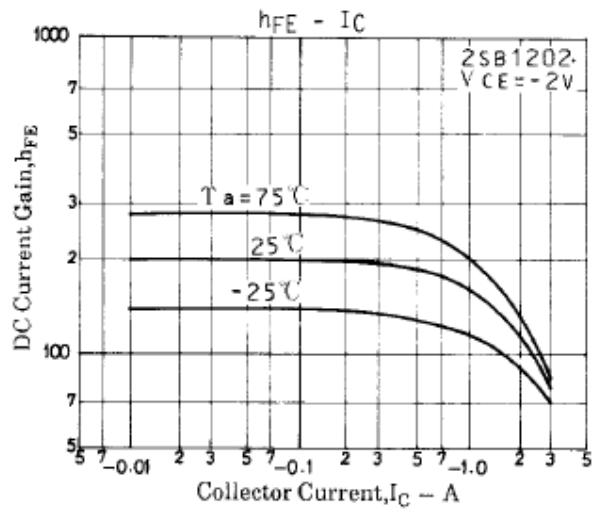
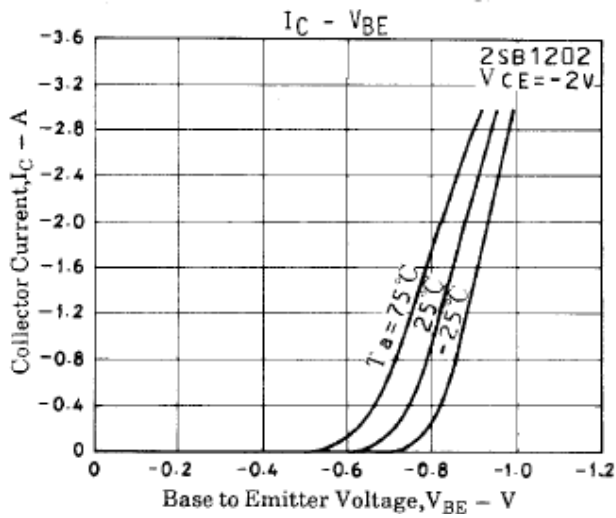
Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



PNP Epitaxial Planar Silicon Transistors

2SB1202



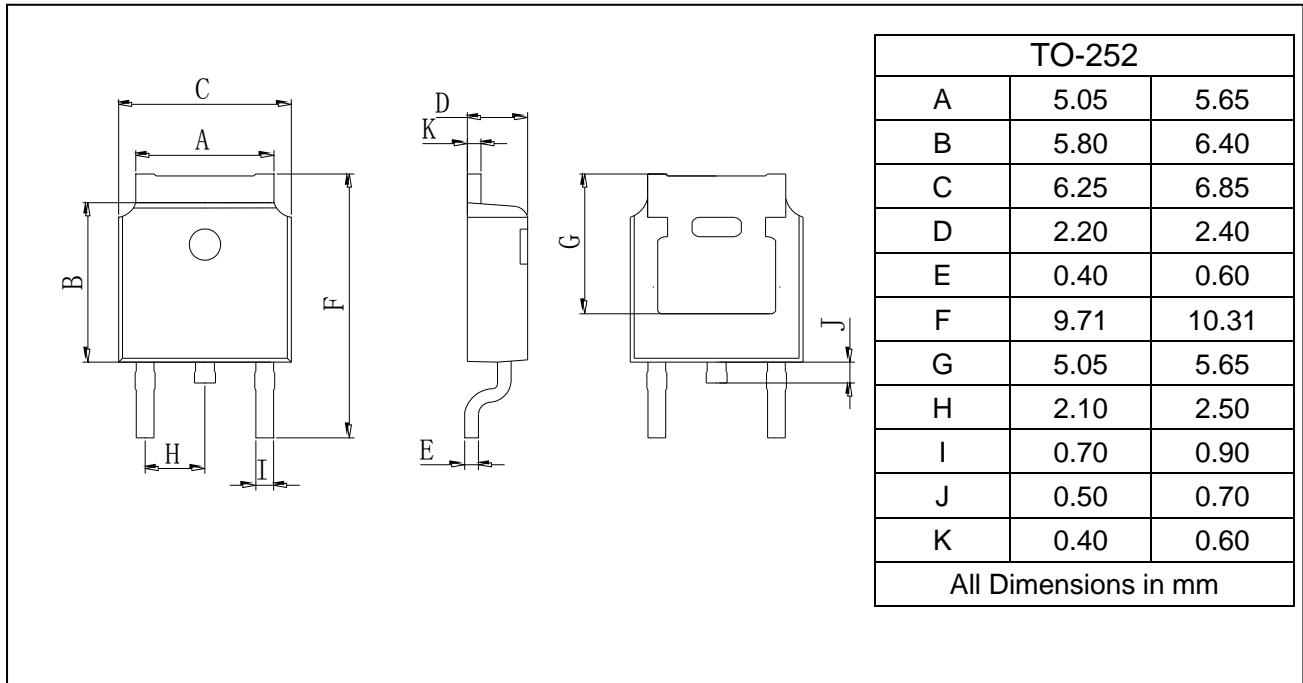
PNP Epitaxial Planar Silicon Transistors

2SB1202

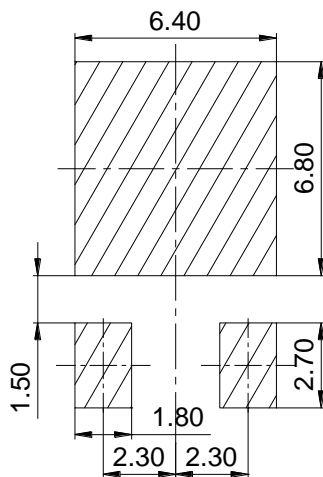
PACKAGE OUTLINE

Plastic surface mounted package

TO-252



SOLDERING FOOTPRINT



Unit: mm